Dual Very Low Noise Amplifier

Features

- Voltage noise of only 1.9nV/√Hz
- Current noise of only $1.2pA/\sqrt{Hz}$
- Bandwidth (-3dB) of 115MHz $@A_V = +2$
- Gain-of-2 stable
- Just 4.8mA per amplifier
- 8-pin MSOP package
- ±2.5V to ±12V operation

Applications

- · ADSL receivers
- · HDSLII receivers
- · Ultrasound input amplifiers
- · Wideband instrumentation
- Communications equipment
- · AGC & PLL active filters
- · Wideband sensors

Ordering Information

Part No.	Package	Tape & Reel	Outline #	
EL2227CY	8-Pin MSOP	-	MDP0043	
EL2227CY-T13	8-Pin MSOP	13"	MDP0043	
EL2227CY-T7	8-Pin MSOP	7"	MDP0043	
EL2227CS	8-Pin SO	-	MDP0027	
EL2227CS-T13	8-Pin SO	13"	MDP0027	
EL2227CS-T7	8-Pin SO	7"	MDP0027	

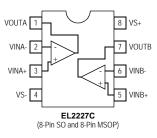
General Description

The EL2227C is a dual, low-noise amplifier, ideally suited to line receiving applications in ADSL and HDSLII designs. With low noise specification of just 1.9 nV/Hz and 1.2 pA/Hz, the EL2227C is perfect for the detection of very low amplitude signals.

The EL2227C features a -3dB bandwidth of 115MHz and is gain-of-2 stable. The EL2227C also affords minimal power dissipation with a supply current of just 4.8mA per amplifier. The amplifier can be powered from supplies ranging from ± 2.5 V to ± 12 V.

The EL2227C is available in a space-saving 8-pin MSOP package as well as the industry-standard 8-pin SO. It can operate over the -40°C to +85°C temperature range.

Connection Diagram



Note: All information contained in this data sheet has been carefully checked and is believed to be accurate as of the date of publication; however, this data sheet cannot be a "controlled document". Current revisions, if any, to these specifications are maintained at the factory and are available upon your request. We recommend checking the revision level before finalization of your design documentation.

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Absolute Maximum Ratings (T_A = 25°C)

Values beyond absolute maximum ratings can cause the device to be prematurely damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied

Maximum Continuous Output Current 40mA

Important Note:

All parameters having Min/Max specifications are guaranteed. Typ values are for information purposes only. Unless otherwise noted, all tests are at the specified temperature and are pulsed tests, therefore: $T_J = T_C = T_A$.

Maximum Die Temperature

Storage Temperature

Power Dissipation

ESD Voltage

Operating Temperature

150°C

-65°C to +150°C

-40°C to +85°C

See Curves

Electrical Characteristics

 $V_S + = +12V, V_S - = -12V, R_L = 500\Omega \ and \ C_L = 3pF \ to \ 0V, R_F = R_G = 620\Omega, and \ T_A = 25^{\circ}C \ unless \ otherwise \ specified.$

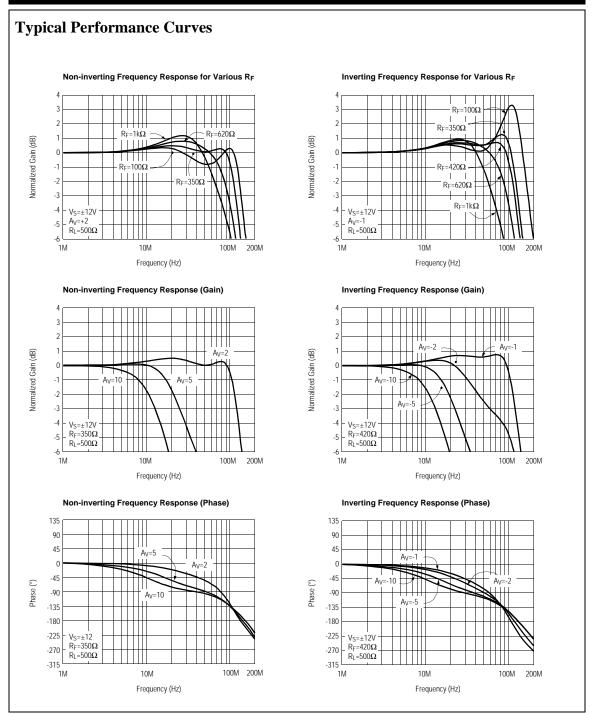
Parameter	Description	Condition	Min	Тур	Max	Unit
Input Chara	cteristics					
Vos	Input Offset Voltage	$V_{CM} = 0V$		-0.2	3	mV
TCVOS	Average Offset Voltage Drift	[1]		-0.6		μV/°C
I _B	Input Bias Current	$V_{CM} = 0V$	-9	-3.4		μΑ
R _{IN}	Input Impedance			7.3		ΜΩ
CIN	Input Capacitance			1.6		pF
CMIR	Common-Mode Input Range		-11.8		+10.4	V
CMRR	Common-Mode Rejection Ratio	for V _{IN} from -11.8V to 10.4V	60	94		dB
A _{VOL}	Open-Loop Gain	$-5V \le V_{OUT} \le 5V$	70	87		dB
en	Voltage Noise	f = 100kHz		1.9		nV/√Hz
i _n	Current Noise	f = 100kHz		1.2		pA/√Hz
Output Char	racteristics			•	•	
V _{OL}	Output Swing Low	$R_L = 500\Omega$		-10.4	-10	V
		$R_L = 250\Omega$		-9.8	-9	V
V _{OH}	Output Swing High	$R_L = 500\Omega$	10	10.4		V
		$R_L = 250\Omega$	9.5	10		V
I _{SC}	Short Circuit Current	$R_L = 10\Omega$	140	180		mA
Power Suppl	ly Performance	·				
PSRR	Power Supply Rejection Ratio	V _S is moved from ±2.25V to ±12V	65	95		dB
Is	Supply Current (Per Amplifier)	No Load		4.8	6.5	mA
V _S	Operating Range		±2.5		±12	V
Dynamic Per	rformance	·				
SR	Slew Rate ^[2]	±2.5V square wave, measured 25%-75%	40	50		V/µS
ts	Settling to 0.1% ($A_V = +2$)	$(A_V = +2), V_{O} = \pm 1V$		65		ns
BW	-3dB Bandwidth	$R_F = 358\Omega$		115		MHz
HD2	2nd Harmonic Distortion	$f = 1MHz, V_O = 2V_{P-P}, R_L = 500\Omega, R_F = 358\Omega$		93		dBc
		$f = 1MHz, V_O = 2V_{P-P}, R_L = 150\Omega, R_F = 358\Omega$		83		dBc
HD3	3rd Harmonic Distortion	$f = 1MHz, V_O = 2V_{P-P}, R_L = 500\Omega, R_F = 358\Omega$		94		dBc
		$f = 1MHz$, $V_O = 2V_{P-P}$, $R_L = 150\Omega$, $R_F = 358\Omega$	ĺ	76		dBc

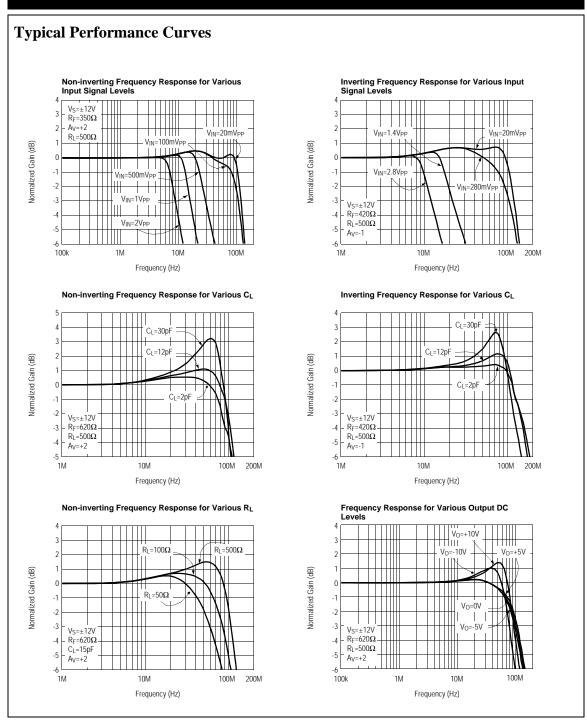
Electrical Characteristics

 $V_{S}+=+5V,\,V_{S}-=-5V,\,R_{L}=500\Omega\text{ and }C_{L}=3pF\text{ to }0V,\,R_{F}=620\Omega\text{ \& }T_{A}=25^{\circ}\text{C unless otherwise specified.}$

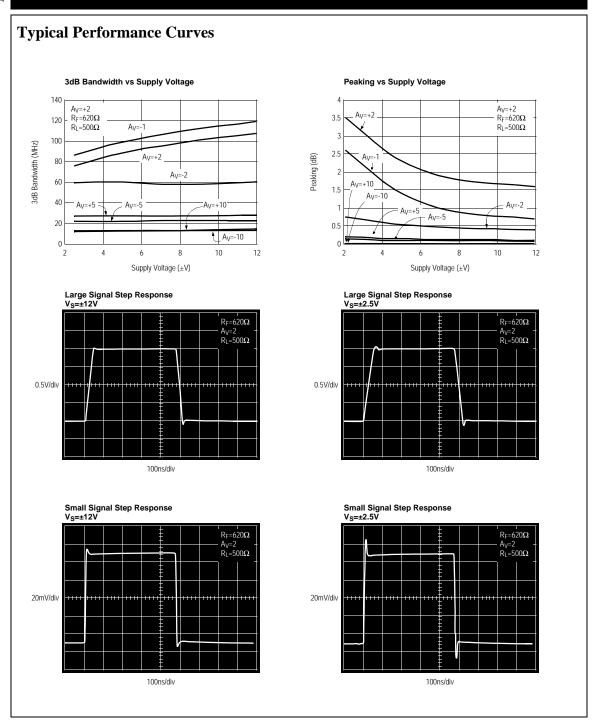
Parameter	Description	Condition	Min	Тур	Max	Unit
Input Chara	cteristics		•			
Vos	Input Offset Voltage	$V_{CM} = 0V$		0.2	3	mV
TCVOS	Average Offset Voltage Drift	[1]		-0.6		μV/°C
I _B	Input Bias Current	$V_{CM} = 0V$	-9	-3.7		μΑ
R _{IN}	Input Impedance			7.3		ΜΩ
C _{IN}	Input Capacitance			1.6		pF
CMIR	Common-Mode Input Range		-4.8		3.4	V
CMRR	Common-Mode Rejection Ratio	for V _{IN} from -4.8V to 3.4V	60	97		dB
A _{VOL}	Open-Loop Gain	$-5V \le V_{OUT} \le 5V$	70	84		dB
e _n	Voltage Noise	f = 100kHz		1.9		nV/√Hz
in	Current Noise	f = 100kHz		1.2		pA/√Hz
Output Char	racteristics		•	•	•	
V _{OL}	Output Swing Low	$R_L = 500\Omega$		-3.8	-3.5	V
		$R_L = 250\Omega$		-3.7	-3.5	V
V_{OH}	Output Swing High	$R_L = 500\Omega$	3.5	3.7		V
		$R_L = 250\Omega$	3.5	3.6		V
I _{SC}	Short Circuit Current	$R_L = 10\Omega$	60	100		mA
Power Suppl	ly Performance	•				
PSRR	Power Supply Rejection Ratio	V _S is moved from ±2.25V to ±12V	65	95		dB
I _S	Supply Current (Per Amplifier)	No Load		4.5	5.5	mA
V _S	Operating Range		±2.5		±12	V
Dynamic Per		-				
SR	Slew Rate ^[2]	±2.5V square wave, measured 25%-75%	35	45		V/µS
t_S	Settling to 0.1% ($A_V = +2$)	$(A_V = +2), V_{O} = \pm 1V$		77		ns
BW	-3dB Bandwidth	$R_F = 358\Omega$		90		MHz
HD2	2nd Harmonic Distortion	$f = 1MHz, V_O = 2V_{P-P}, R_L = 500\Omega, R_F = 358\Omega$		98		dBc
		$f = 1MHz, V_O = 2V_{P-P}, R_L = 150\Omega, R_F = 358\Omega$		90		dBc
HD3	3rd Harmonic Distortion	$f = 1MHz, V_O = 2V_{P-P}, R_L = 500\Omega, R_F = 358\Omega$		94		dBc
		$f = 1MHz, V_O = 2V_{P-P}, R_L = 150\Omega, R_F = 358\Omega$		79		dBc

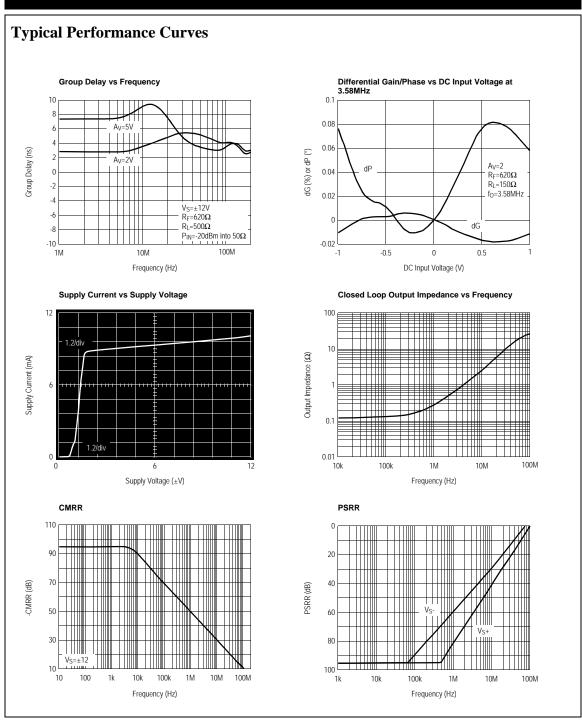
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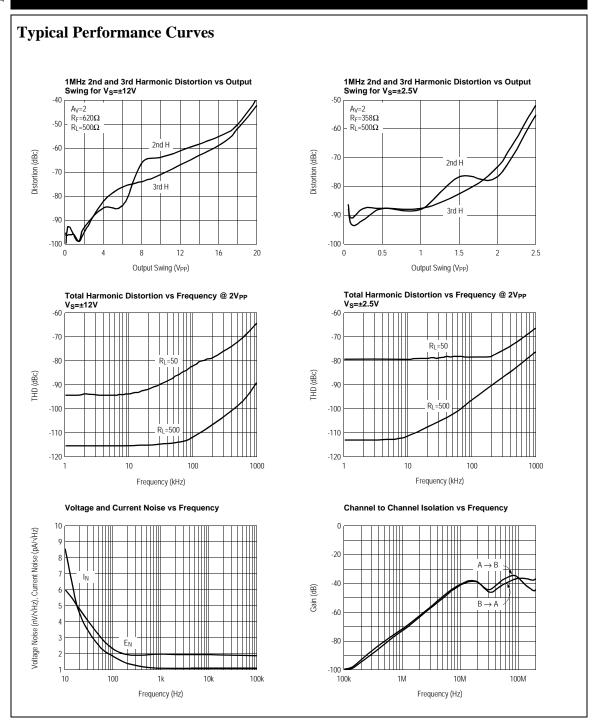


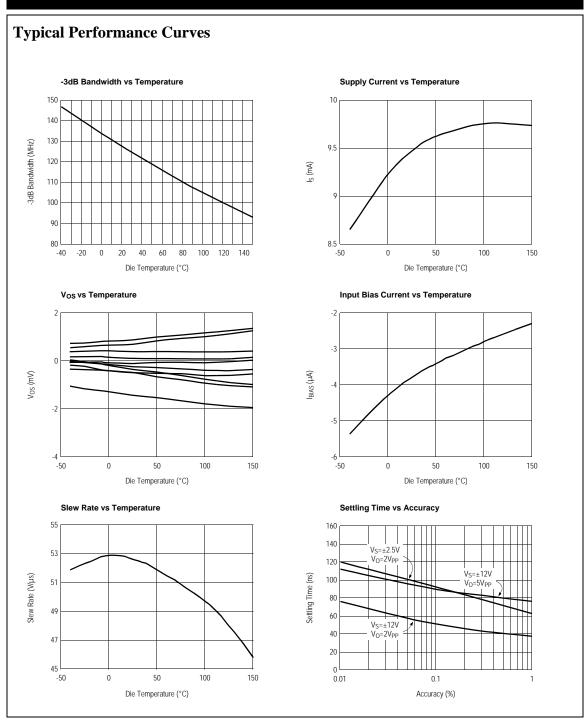
Dual Very Low Noise Amplifier



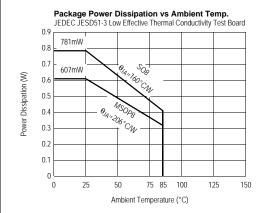


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Typical Performance Curves



Pin Descriptions

	•			
EL2227CY 8-Pin MSOP	EL2227CS 8-Pin SO	Pin Name	Pin Function	Equivalent Circuit
				Equivalent Circuit
1	1	VOUTA	Output	V _{S+}
				Circuit 1
2	2	VINA-	Input	V _{IN} + V _{IN} - V _{IN} - Circuit 2
3	3	VINA+	Input	Reference Circuit 2
4	4	VS-	Supply	
5	5	VINB+	Input	
6	6	VINB-	Input	Reference Circuit 2
7	7	VOUTB	Output	Reference Circuit 1
8	8	VS+	Supply	

Applications Information

Product Description

The EL2227C is a dual voltage feedback operational amplifier designed especially for DMT ADSL and other applications requiring very low voltage and current noise. It also features low distortion while drawing moderately low supply current and is built on Elantec's proprietary high-speed complementary bipolar process. The EL2227C use a classical voltage-feedback topology which allows them to be used in a variety of applications where current-feedback amplifiers are not appropriate because of restrictions placed upon the feedback element used with the amplifier. The conventional topology of the EL2227C allows, for example, a capacitor to be placed in the feedback path, making it an excellent

choice for applications such as active filters, sampleand-holds, or integrators.

ADSL CPE Applications

The low noise EL2227C amplifier is specifically designed for the dual differential receiver amplifier function with ADSL transceiver hybrids as well as other low-noise amplifier applications. A typical ADSL CPE line interface circuit is shown in Figure 1. The EL2227C is used in receiving DMT down stream signal. With careful transceiver hybrid design and the EL2227C 1.9 nV/VHz voltage noise and 1.2 pA/VHz current noise performance, -140dBm/Hz system background noise performance can be easily achieved.

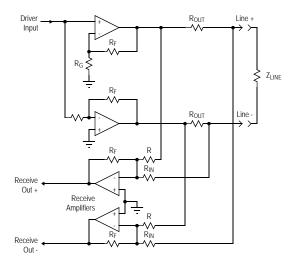
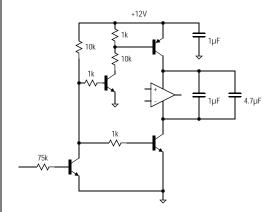


Figure 1. Typical Line Interface Connection

Disable Function

The EL2227C is in the standard dual amplifier package without the enable/disable function. A simple way to implement the enable/disable function is depicted below. When disabled, both the positive and negative supply voltages are disconnected (see Figure 2 below.)



Power Dissipation

With the wide power supply range and large output drive capability of the EL2227C, it is possible to exceed the 150°C maximum junction temperatures under certain load and power-supply conditions. It is therefore important to calculate the maximum junction temperature (T_{JMAX}) for all applications to determine if power supply voltages, load conditions, or package type need to be modified for the EL2227C to remain in the safe operating area. These parameters are related as follows:

$$\mathbf{T}_{\mathrm{JMAX}} \, = \, \mathbf{T}_{\mathrm{MAX}} + (\boldsymbol{\theta}_{\mathrm{JA}} \! \times \! \mathrm{PD}_{\mathrm{MAXTOTAL}})$$

where:

 $PD_{MAXTOTAL}$ is the sum of the maximum power dissipation of each amplifier in the package ($PD_{MAX}\!)$

PD_{MAX} for each amplifier can be calculated as follows:

$$PD_{MAX} = 2 \times V_S \times I_{SMAX} + (V_S - V_{OUTMAX}) \times \frac{V_{OUTMAX}}{R_L}$$

where:

T_{MAX} = Maximum Ambient Temperature

 θ_{JA} =Thermal Resistance of the Package

 $PD_{MAX} = \!\! Maximum \; Power \; Dissipation \; of \; 1 \; Amplifier \;$

V_S =Supply Voltage

 I_{MAX} =Maximum Supply Current of 1 Amplifier

V_{OUTMAX}=Maximum Output Voltage Swing of the Application

R_L =Load Resistance

To serve as a guide for the user, we can calculate maximum allowable supply voltages for the example of the video cable-driver below since we know that $T_{JMAX}=150^{\circ}C,\,T_{MAX}=75^{\circ}C,\,I_{SMAX}=9.5\text{mA},$ and the package $\theta_{JA}s$ are shown in Table 1. If we assume (for this example) that we are driving a back-terminated video cable, then the maximum average value (over duty-cycle) of V_{OUTMAX} is 1.4V, and $R_L=150\Omega,$ giving the results seen in Table 1.

Table 1

Part	Package	$\theta_{\mathbf{J}\mathbf{A}}$	Max PD _{ISS} @ T _{MAX}	Max V _S
EL2227CS	SO8	160°C/W	0.406W @ 85°C	
EL2227CY	MSOP8	206°C/W	0.315W @ 85°C	

Single-Supply Operation

The EL2227C have been designed to have a wide input and output voltage range. This design also makes the EL2227C an excellent choice for single-supply operation. Using a single positive supply, the lower input voltage range is within 200mV of ground ($R_L=500\Omega$), and the lower output voltage range is within 875mV of ground. Upper input voltage range reaches 3.6V, and output voltage range reaches 3.8V with a 5V supply and $R_L=500\Omega$. This results in a 2.625V output swing on a single 5V supply. This wide output voltage range also allows single-supply operation with a supply voltage as high as 28V.

Gain-Bandwidth Product and the -3dB Bandwidth

The EL2227C have a gain-bandwidth product of 137MHz while using only 5mA of supply current per amplifier. For gains greater than 2, their closed-loop -3dB bandwidth is approximately equal to the gain-

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bandwidth product divided by the noise gain of the circuit. For gains less than 2, higher-order poles in the amplifiers' transfer function contribute to even higher closed loop bandwidths. For example, the EL2227C have a -3dB bandwidth of 115MHz at a gain of +2, dropping to 28MHz at a gain of +5. It is important to note that the EL2227C have been designed so that this "extra" bandwidth in low-gain applications does not come at the expense of stability. As seen in the typical performance curves, the EL2227C in a gain of +2 only exhibit 0.5dB of peaking with a 1000 Ω load.

Output Drive Capability

The EL2227C have been designed to drive low impedance loads. They can easily drive $6V_{PP}$ into a 500Ω load. This high output drive capability makes the EL2227C an ideal choice for RF, IF and video applications.

Printed-Circuit Layout

The EL2227C are well behaved, and easy to apply in most applications. However, a few simple techniques will help assure rapid, high quality results. As with any high-frequency device, good PCB layout is necessary for optimum performance. Ground-plane construction is highly recommended, as is good power supply bypassing. A 0.1µF ceramic capacitor is recommended for bypassing both supplies. Lead lengths should be as short as possible, and bypass capacitors should be as close to the device pins as possible. For good AC performance, parasitic capacitances should be kept to a minimum at both inputs and at the output. Resistor values should be kept under $5k\Omega$ because of the RC time constants associated with the parasitic capacitance. Metal-film and carbon resistors are both acceptable, use of wire-wound resistors is not recommended because of their parasitic inductance. Similarly, capacitors should be low-inductance for best performance.

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